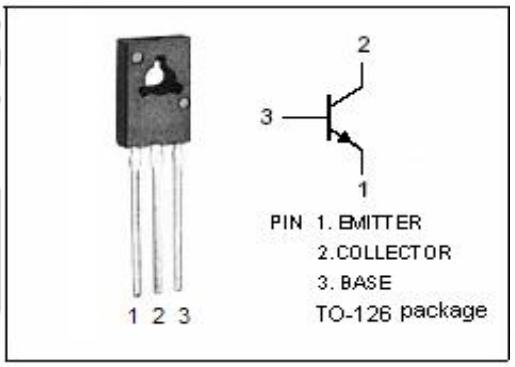
isc Silicon NPN Power Transistor MJE521

DESCRIPTION

- Collector–Emitter Sustaining Voltage–
  : $V_{CEO(SUS)}$ = 40 V(Min)
- DC Current Gain–
  : h_{FE} = 40(Min) @ I_C= 1A
- Complement to Type MJE371

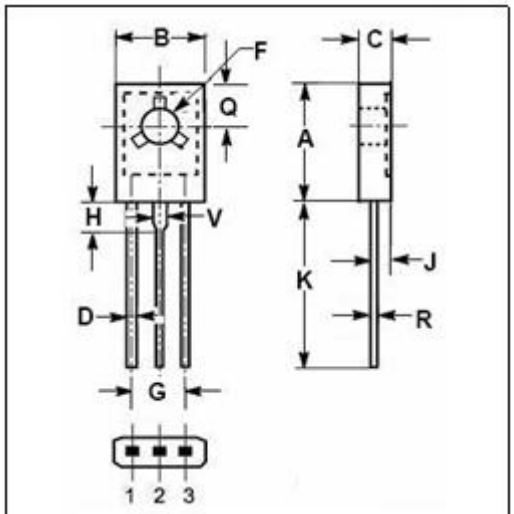
APPLICATIONS

- Designed for use in general−purpose amplifier and switching circuits applications.



ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation T_C=25℃	40	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	3.12	℃/W

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ELECTRICAL CHARACTERISTICS

T_C =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA; I_B= 0	40		V
I_{CBO}	Collector Cutoff Current	V_{CB}= 30V; I_E= 0		0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0		0.1	mA
h_{FE}	DC Current Gain	I_C= 1 A ; V_{CE}= 1V	40		